

Appln No. 09/693,484
Amdt. Dated November 12, 2000
Reply to Office action of September 17, 2003

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Amendments to the Specification:**Paragraph beginning at Page 5, lines 28-31, to be amended as follows:**

C¹
The carrier 10 is formed from the same material as the integrated circuit 14. Accordingly, the carrier 10 is formed of silicon having an insulating layer of silicon dioxide. The insulating layer (54) also serves as a hard mask for etching the serpentine members 22, as will be discussed in greater detail below.

Paragraph beginning at Page 5, line 34 to Page 6, line 4, to be amended as follows:

C²
It is to be noted that the version of the carrier 10 shown in Figure 10 of the drawings is where the receiving zone 12 is on the same side of the carrier 10 as the pads 18 as shown in Figure 7 of the drawings. Where the receiving zone 12 is on an opposite surface of the carrier 10, as shown in Figure 8 of the drawings, the circuitry layer (48) is applied to both sides of the wafer 46. This is shown on a smaller scale in Figure 9 of the drawings. In this embodiment, each track 52 is electrically connected to its associated pad 18 via a plated through hole 58 extending through the wafer 46.